

NEC**SILICON TRANSISTOR**
2SA1385-Z**PNP SILICON EPITAXIAL TRANSISTOR**
MP-3**DESCRIPTION**

2SA1385-Z is designed for Audio Frequency Amplifier and Switching, especially in Hybrid Integrated Circuits.

FEATURES

- Low $V_{CE(sat)}$: $V_{CE(sat)} = -0.18$ V TYP.
- Complement to 2SC3518-Z

QUALITY GRADE

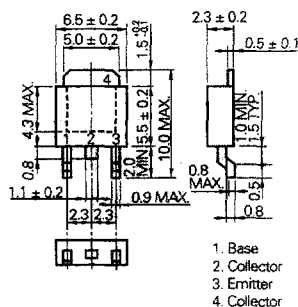
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Collector to Base Voltage	V_{CB0}	-60	V
Collector to Emitter Voltage	V_{CE0}	-60	V
Emitter to Base Voltage	V_{EB0}	-7	V
Collector Current (DC)	I_C	-5	A
Collector Current (Pulse)*	I_C	-7	A
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_T	10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10$ ms, Duty Cycle ≤ 50 %

PACKAGE DIMENSIONS
(in millimeters)

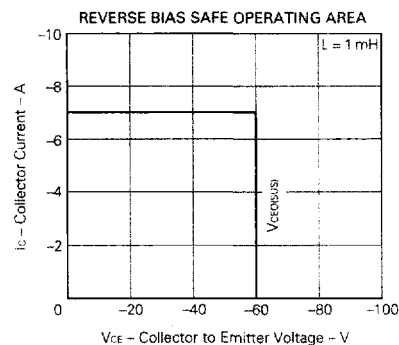
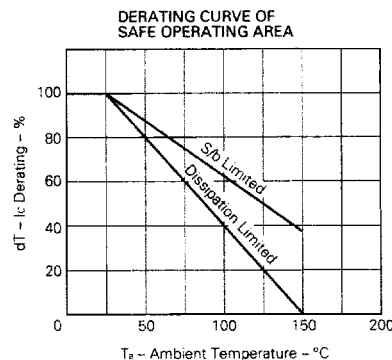
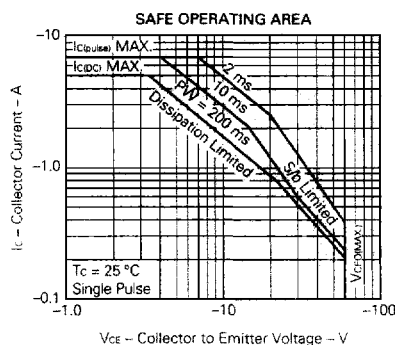
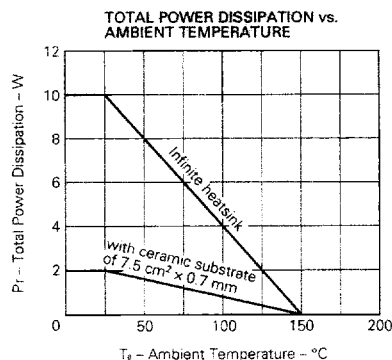
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			-10	μA	$V_{CB} = -50\text{ V}, I_E = 0$
Emitter Cutoff Current	I_{EBO}			-10	μA	$V_{EB} = -7.0\text{ V}, I_C = 0$
DC Current Gain	h_{FE1}^*	100	200	400		$V_{CE} = -1.0\text{ V}, I_C = -2.0\text{ A}$
DC Current Gain	h_{FE2}^*	50	100			$V_{CE} = -1.0\text{ V}, I_C = -5.0\text{ A}$
Collector Saturation Voltage	$V_{CE(sat)}^*$		-0.18	-0.3	V	$I_C = -2.0\text{ A}, I_B = -0.2\text{ A}$
Base Saturation Voltage	$V_{BE(sat)}^*$			-1.2	V	$I_C = -2.0\text{ A}, I_B = -0.2\text{ A}$
Gain Bandwidth Product	f_T		140		MHz	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}$
Turn-on Time	t_{on}		0.08	1.0	μs	$I_C = -2.0\text{ A}, V_{CE} = -10\text{ V}$
Storage Time	t_{stg}		0.55	2.5	μs	$R_L = 50\ \Omega$
Fall time	t_f		0.18	1.0	μs	$I_{B1} = -I_{B2} = -0.2\text{ A}$

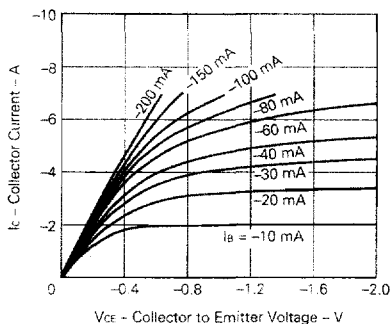
* Pulsed: $PW \leq 350\ \mu\text{s}$, Duty Cycle $\leq 2\%$

hFE Classification

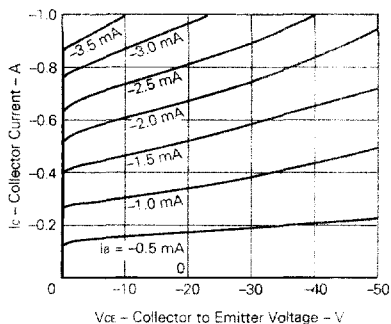
MARKING	M	L	K
h_{FE1}	100 to 200	160 to 320	200 to 400

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

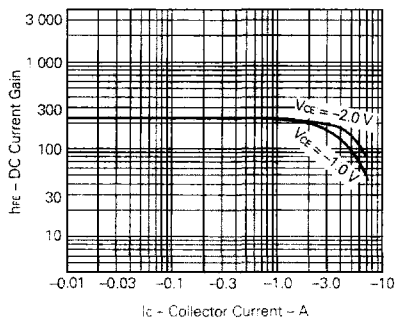
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



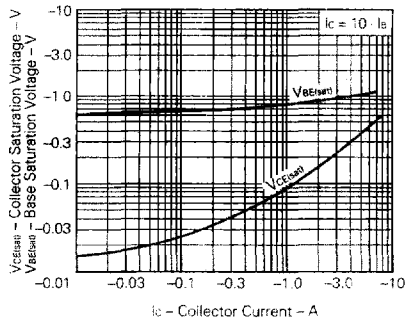
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



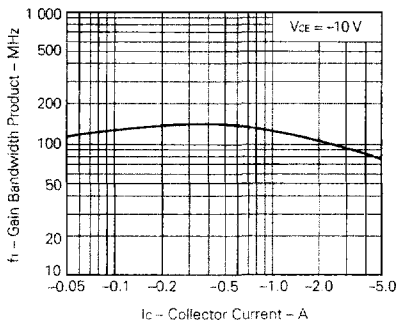
DC CURRENT GAIN vs. COLLECTOR CURRENT



COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



SWITCHING TIME vs. COLLECTOR CURRENT

